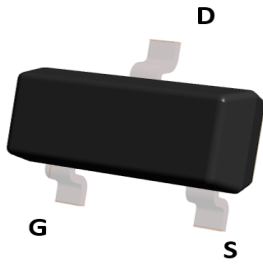
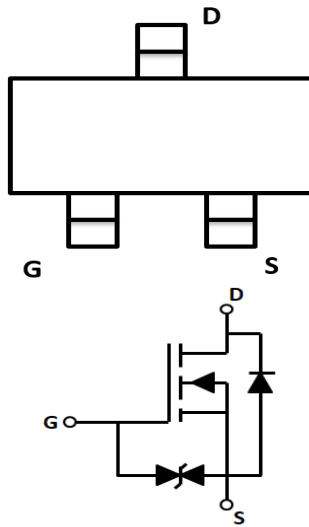


## N-Channel Enhancement Mode Field Effect Transistor



Top View

**SOT-523**



### Product Summary

- $V_{DS}$  60V
- $I_D$  100mA
- $R_{DS(ON)}$  ( at  $V_{GS}=10V$ )  $< 8.0 \Omega$
- $R_{DS(ON)}$  ( at  $V_{GS}=4.5V$ )  $< 13.0 \Omega$
- ESD Protected Up to 2.0KV (HBM)

### General Description

- Trench Power LV MOSFET technology
- High Power and current handling capability

### Applications

- Load/Power Switching
- Interfacing Switching
- Logic Level Shift

### ■ Absolute Maximum Ratings ( $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-source Voltage	$V_{DS}$	60	V
Gate-source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current	$I_D$	100	mA
Pulsed Drain Current <sup>A</sup>	$I_{DM}$	1.5	A
Total Power Dissipation @ $T_A=25^\circ\text{C}$	$P_D$	0.15	W
Thermal Resistance Junction-to-Ambient @ Steady State	$R_{\theta JA}$	357	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55~+150	$^\circ\text{C}$

## ■ Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
<b>Static Parameter</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> =250μA	60			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V			1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> =0V			±10	μA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> =250μA	0.8	1.5	2.2	V
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> =100mA		2.5	8.0	Ω
		V <sub>GS</sub> = 4.5V, I <sub>D</sub> =10mA		3.0	13.0	
Diode Forward Voltage <sup>C</sup>	V <sub>SD</sub>	I <sub>S</sub> =100mA, V <sub>GS</sub> =0V			1.2	V
Maximum Body-Diode Continuous Current	I <sub>S</sub>				100	mA
<b>Dynamic Parameters <sup>B</sup></b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V, f=1MHZ			18	pF
Output Capacitance	C <sub>oss</sub>				12	
Reverse Transfer Capacitance	C <sub>rss</sub>				7	
<b>Switching Parameters <sup>B</sup></b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> =10V, V <sub>DS</sub> =30V, I <sub>D</sub> =0.1A		1.7		nC
Gate Source Charge	Q <sub>gs</sub>			0.19		
Gate Drain Charge	Q <sub>gd</sub>			0.27		
Turn-on Delay Time	t <sub>D(on)</sub>	V <sub>GS</sub> =10V, V <sub>DD</sub> =30V, R <sub>G</sub> =6Ω, I <sub>D</sub> =0.1A		5		ns
Turn-off Delay Time	t <sub>D(off)</sub>			17		

A. Repetitive Rating: Pulse width limited by maximum junction temperature.

B. These parameters have no way to verify.

C. Pulse Test: Pulse Width ≤ 300us, Duty Cycle ≤ 0.5%.

## ■ Typical Performance Characteristics

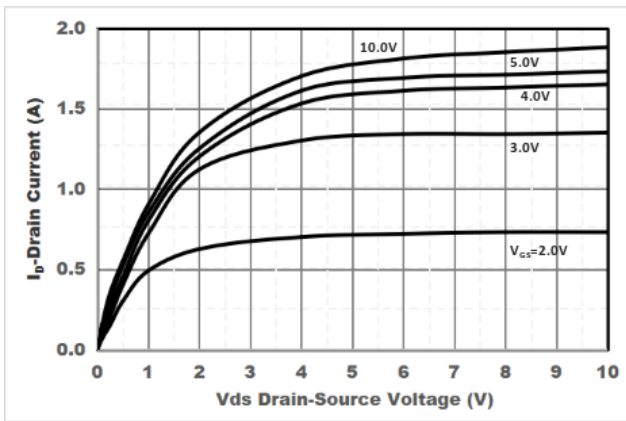


Figure1. Output Characteristics

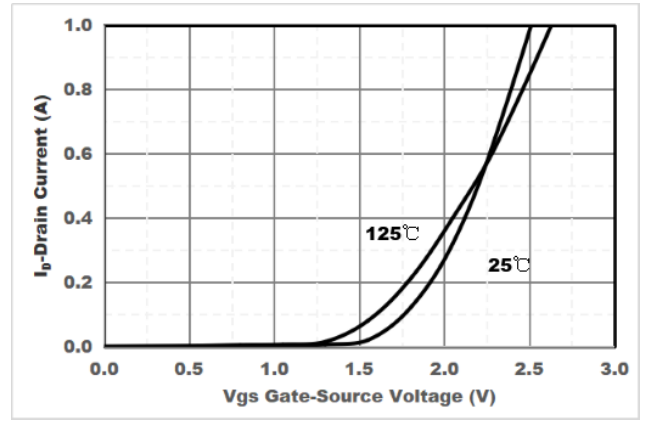


Figure2. Transfer Characteristics

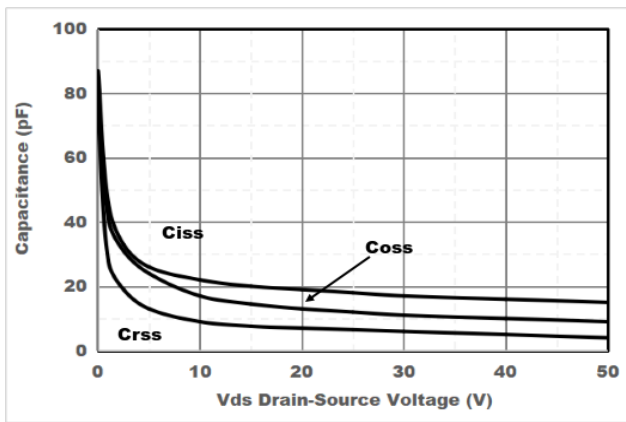


Figure3. Capacitance Characteristics

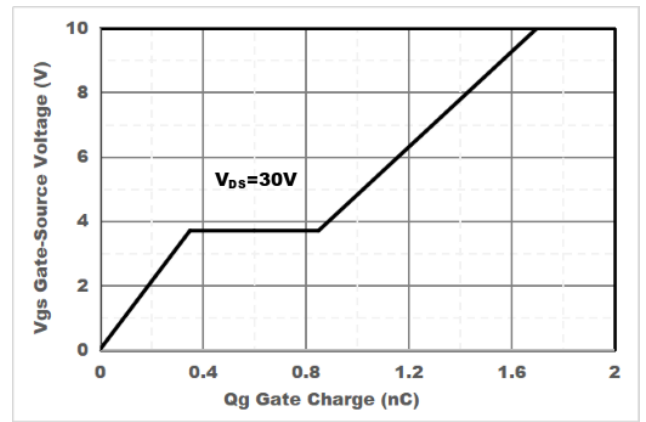


Figure4. Gate Charge

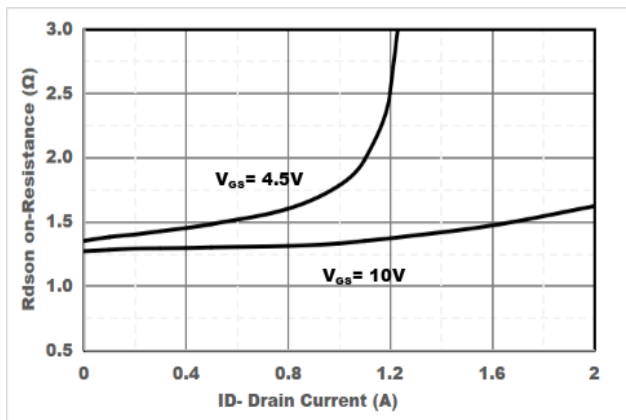


Figure5. Drain-Source on Resistance

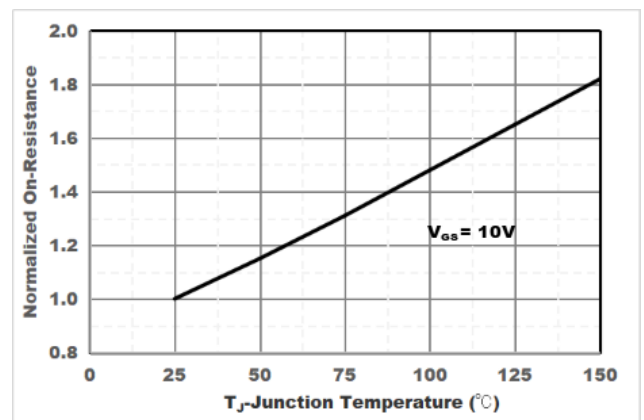


Figure6. Drain-Source on Resistance

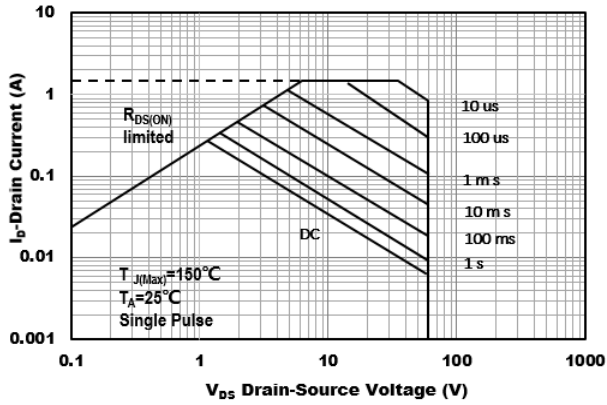


Figure 7. Safe Operation Area

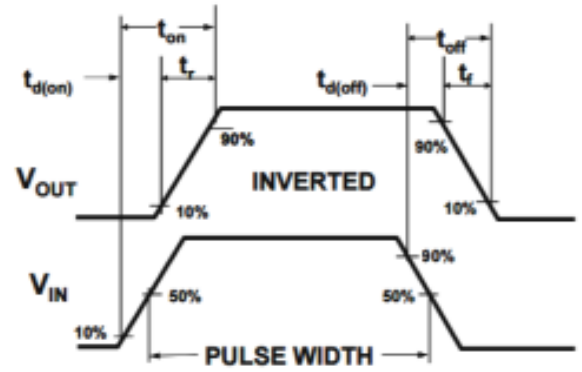
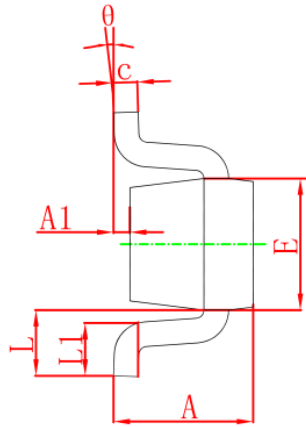
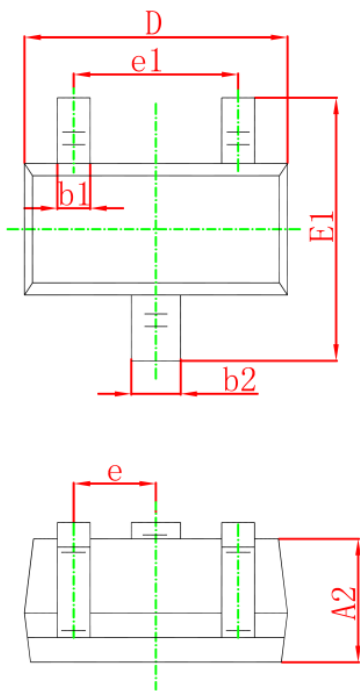


Figure 8. Switching wave

## ■SOT-523 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.350	0.010	0.014
c	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
e	0.500 TYP.		0.020 TYP.	
e1	0.900	1.100	0.035	0.043
L	0.400 REF.		0.016 REF.	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°